**Attachment to PRELIMINARY AMENDMENT**

Paragraph [0005] on Page 2, line 1

**[0005]** U.S. Patent No. [_____] 6,280,697 (Serial No. 09/259,307 entitled "Nanotube-Based High Energy Material and Method") the disclosure of which is incorporated herein by reference, in its entirety, discloses a carbon nanotube-based electron emitter structure.

Paragraph [0014] on page 4, line 4

**[0014]** It has also been shown that the electronic work functions of carbon nanotube materials can be reduced substantially when they are intercalated with alkali metals, such as cesium. See, e.g. - *Ibid.*, and "Effects of Cs Deposition on the Field-emission Properties of Single-walled Carbon Nanotube Bundles," [W.A. Stallcup et al.] A. Wadhawan et al., Appl. Phys. Lett., 78 (No. 1), pp. 108-110, January 1, 2001.

#3

Patent
Attorney's Docket No. 032566-011

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

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| In re Patent Application of | ) | |
| | ) | |
| Otto Z. ZHOU | ) | Group Art Unit: 1745 |
| | ) | |
| Application No.: 09/881,684 | ) | Examiner: Unassigned |
| | ) | |
| Filed: June 18, 2001 | ) | |
| | ) | |
| For: METHOD OF MAKING NANOTBUE-BASED MATERIAL WITH ENHANCED ELECTRON FILED EMISSION PROPERTIES | ) | |

**PRELIMINARY AMENDMENT**

Assistant Commissioner for Patents
Washington, D.C. 20231

Sir:

Prior to examination of the above-captioned patent application, kindly enter the following amendment.

**IN THE SPECIFICATION:**

Please replace paragraph [0005] on page 2 with the following:

**[0005]** U.S. Patent No. 6,280,697 (Serial No. 09/259,307 entitled "Nanotube-Based High Energy Material and Method") the disclosure of which is incorporated herein by reference, in its entirety, discloses a carbon nanotube-based electron emitter structure.

Please replace paragraph [0014] on page 14 with the following:

**[0014]** It has also been shown that the electronic work functions of carbon nanotube materials can be reduced substantially when they are intercalated with alkali metals, such as cesium. See, e.g. - *Ibid.*, and "Effects of Cs Deposition on the Field-